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(54) **METHODS OF FORMING CAPACITOR CONSTRUCTIONS**

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See application file for complete search history.

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(57) **ABSTRACT**

The invention includes capacitor constructions comprising a layer of aluminum oxide between a high-k dielectric material and a layer comprising titanium and nitrogen. The layer comprising titanium and nitrogen can be, for example, titanium nitride and/or boron-doped titanium nitride. The capacitor constructions can be incorporated into DRAM cells, which in turn can be incorporated into electronic systems. The invention also includes methods of forming capacitor constructions.

12 Claims, 3 Drawing Sheets